Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
-30V	8mΩ @ V_{GS} = -10V	-17A
	10.2mΩ @ V_{GS} = -4.5V	-14.5A

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DIODES™ DMP3010LK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

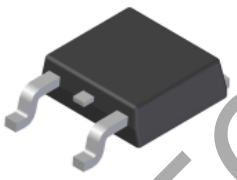
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- DC-DC converters
- Power management functions
- Backlighting

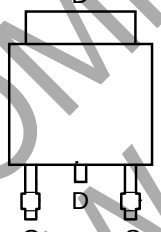
Mechanical Data

- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

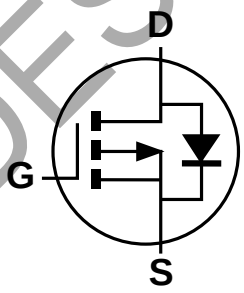
TO252 (DPAK)



Top View



Top View
Pin-Out



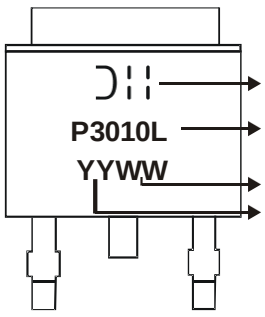
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP3010LK3Q-13	TO252	2,500	Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Manufacturer's Marking Code
Product Type Marking Code
Week Code (01 to 53)
Year Code (ex: 22 = 2022)

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-17.0 -13.0	A
	t < 10s	T_A = +25°C T_A = +70°C	I_D	-27.0 -21.0	A
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-14.5 -11.5	A
	t < 10s	T_A = +25°C T_A = +70°C	I_D	-23.0 -18.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-100	A
Maximum Body Diode Forward Current (Note 6)			I_S	5.5	A
Avalanche Current (Note 7)			I_{AS}	47	A
Avalanche Energy (Note 7)			E_{AS}	113	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	1.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	72	°C/W
	t < 10s		29	°C/W
Total Power Dissipation (Note 6)		P_D	3.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	37	°C/W
	t < 10s		15	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.1	-1.6	-2.1	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	6.5	8	mΩ	V_{GS} = -10V, I_D = -10A
		—	7.2	10.2		V_{GS} = -4.5V, I_D = -10A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	30	—	S	V_{DS} = -15V, I_D = -10A
Diode Forward Voltage	V_{SD}	—	-0.65	-1.0	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	6234	—	pF	V_{DS} = 15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	1500	—		
Reverse Transfer Capacitance	C_{rss}	—	774	—		
Gate Resistance	R_G	—	1.28	—	µ	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	—	59.2	—	nC	V_{DS} = -15V, V_{GS} = -4.5V, I_D = -10A
Gate-Source Charge	Q_{gs}	—	16.1	—		
Gate-Drain Charge	Q_{gd}	—	15.7	—		
Turn-On Delay Time	$t_{D(ON)}$	—	11.4	—	ns	V_{DS} = -15V, V_{GEN} = -10V, R_G = 6Ω, I_D = -1A
Turn-On Rise Time	t_R	—	9.4	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	260.7	—		
Turn-Off Fall Time	t_F	—	99.3	—		

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. UIS in production with L = 0.1mH, T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.

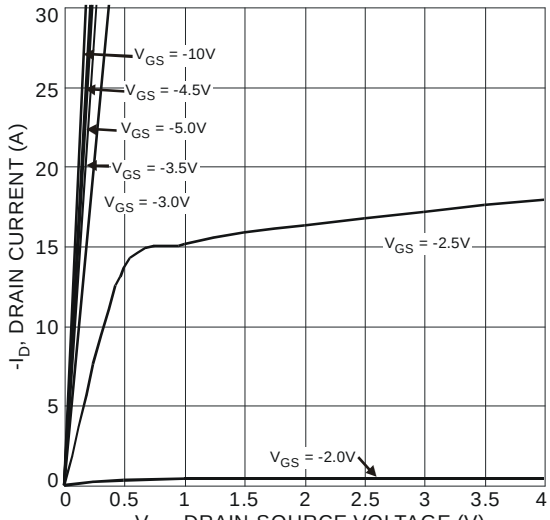


Figure 1 Typical Output Characteristics

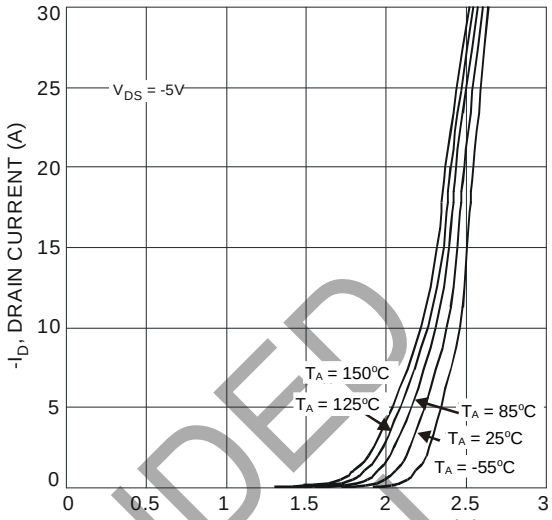


Figure 2 Typical Transfer Characteristics

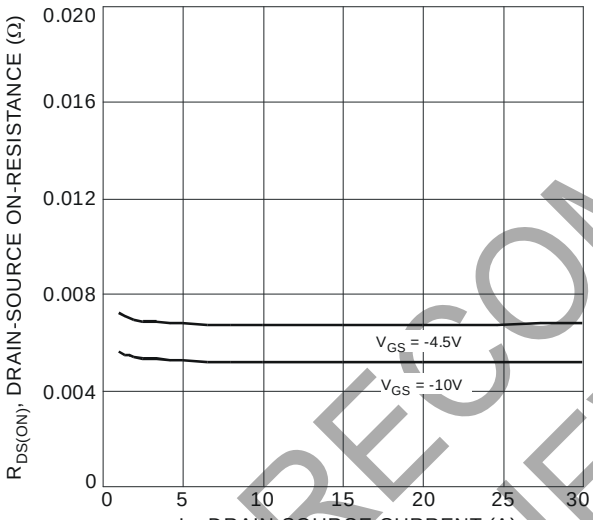


Figure 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

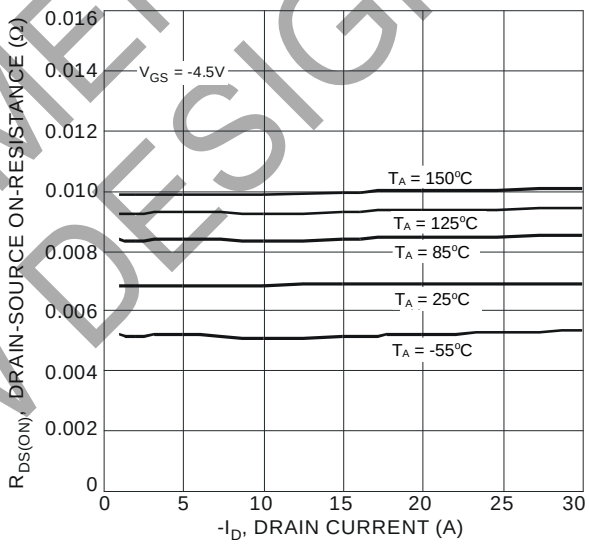


Figure 4 Typical On-Resistance
vs. Drain Current and Temperature

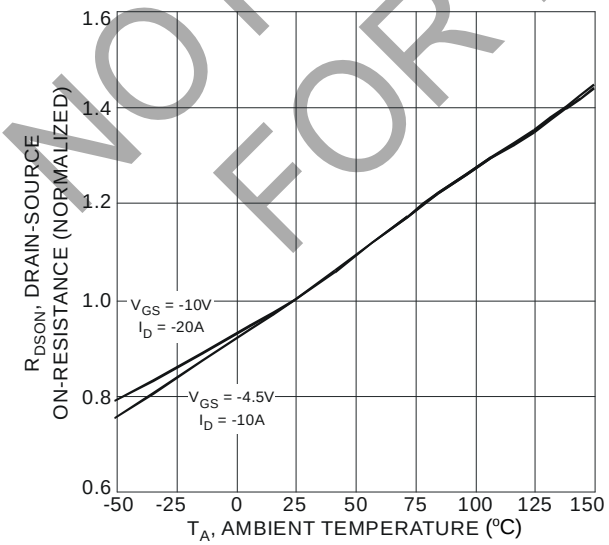


Figure 5 On-Resistance Variation with Temperature

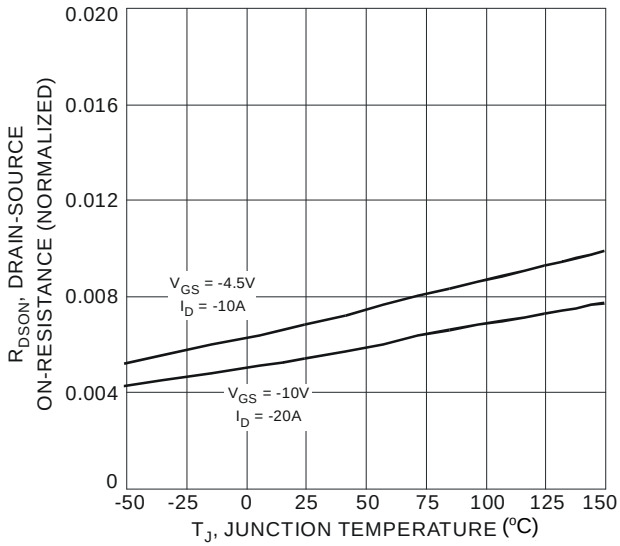


Figure 6 On-Resistance Variation with Temperature

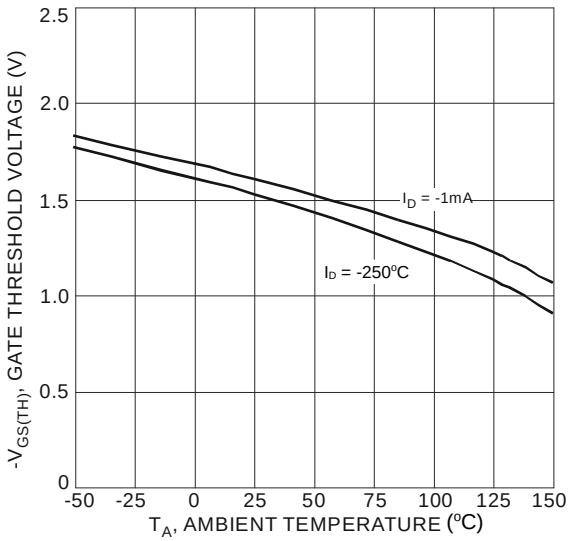


Figure 7 Gate Threshold Variation vs. Ambient Temperature

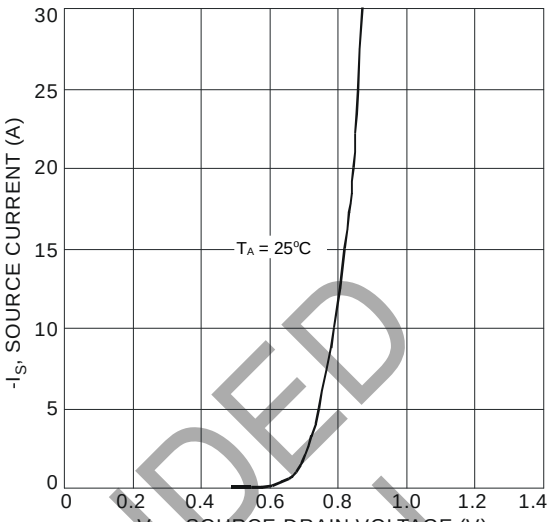


Figure 8 Diode Forward Voltage vs. Current

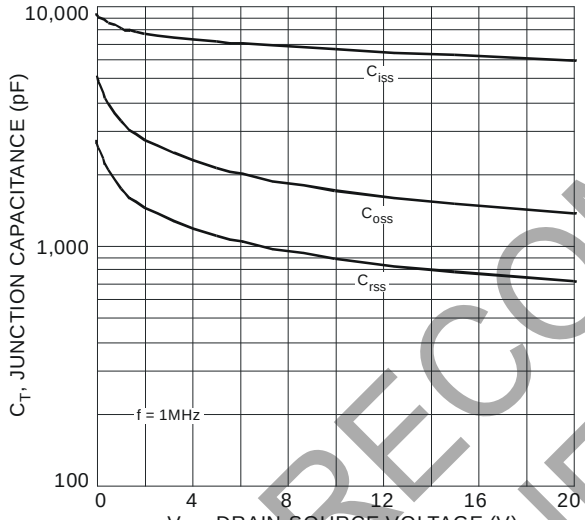


Figure 9 Typical Total Capacitance

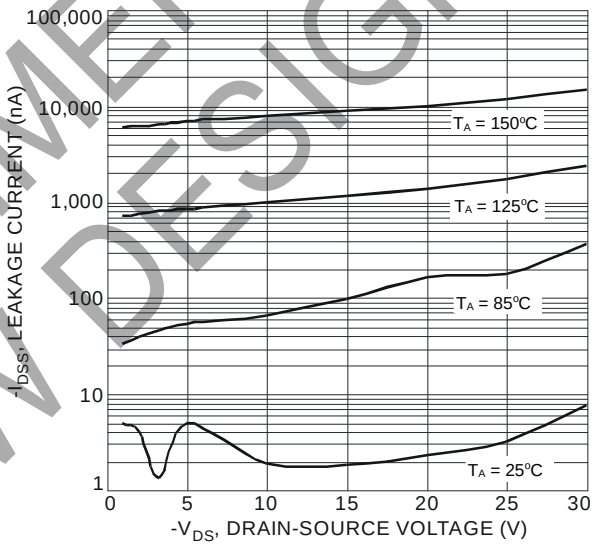


Figure 10 Typical Leakage Current vs. Drain-Source Voltage

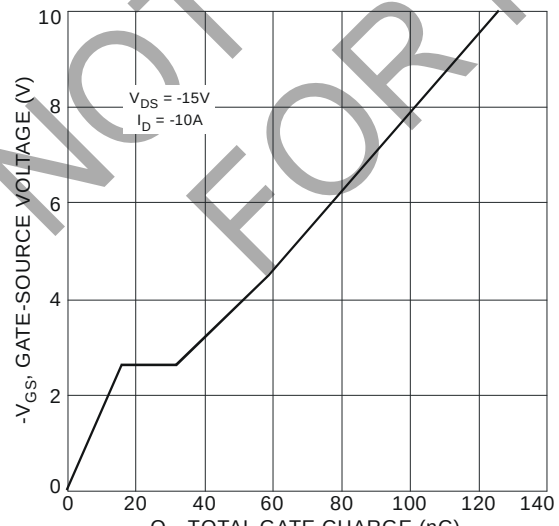


Figure 11 Gate-Source Voltage vs. Total Gate Charge

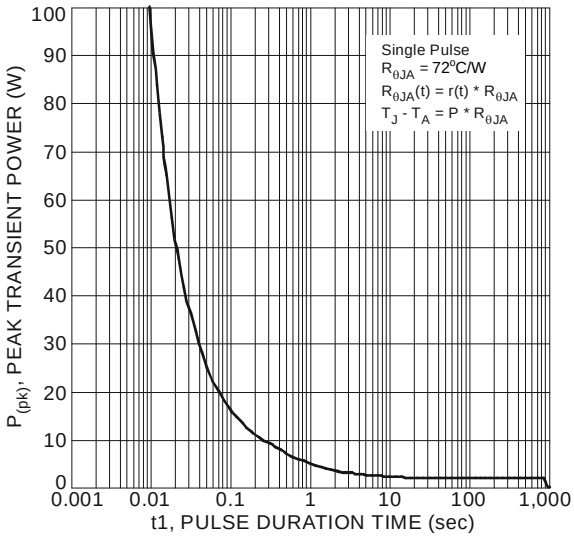


Figure 12 Single Pulse Maximum Power Dissipation

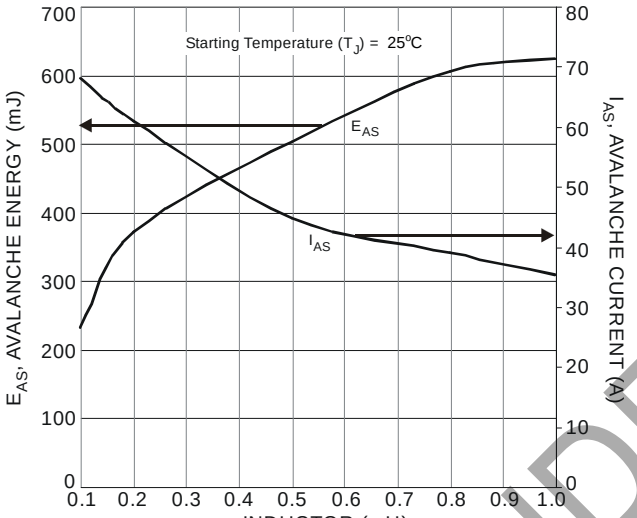


Figure 13 Single-Pulse Avalanche Tested

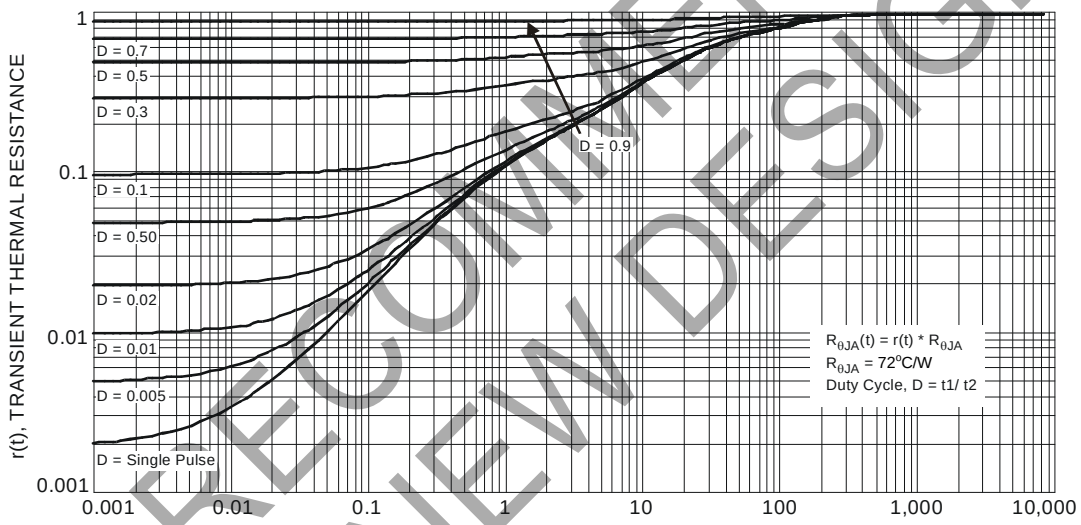
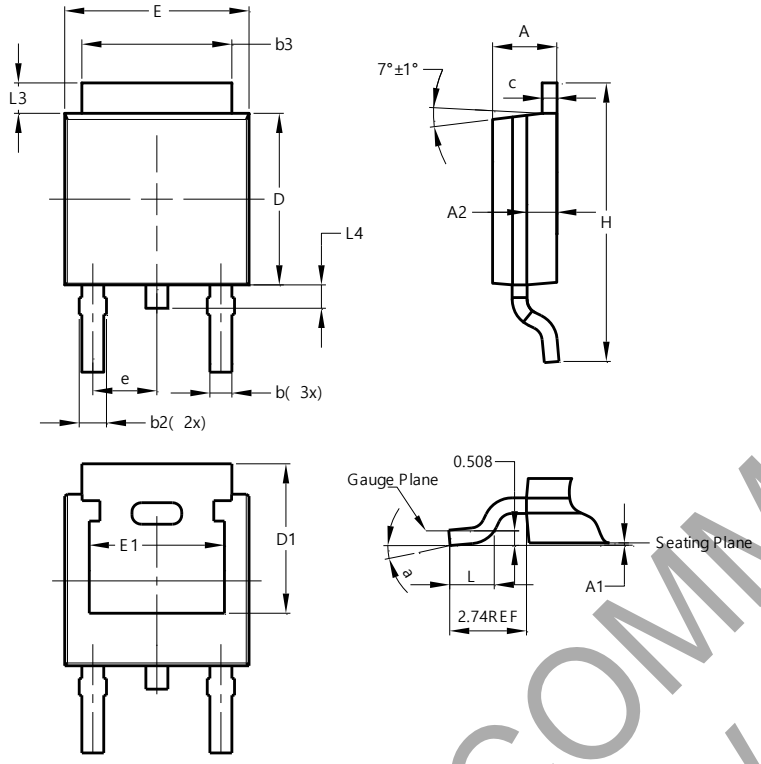


Figure 14 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

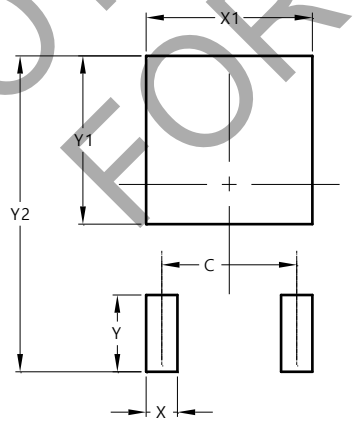


TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.50	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	--	--
e	2.286 BSC		
E	6.45	6.70	6.58
E1	4.32	--	--
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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